

Date:- 10 Oct, 2022

Data Sheet Issue:- A1

Advance Data Insulated Gate Bi-Polar Transistor Type T1375DF65E

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
Vces	Collector – emitter voltage	6500	V
VDC link	Permanent DC voltage for 100 FIT failure rate.	3600	V
Vges	Peak gate – emitter voltage	±20	V

	RATINGS	MAXIMUM LIMITS	UNITS
lc	Continuous DC collector current, IGBT	1375	А
Ісгм	Repetitive peak collector current, t _p =1ms, IGBT	2750	А
IECO	Maximum reverse emitter current, tp=100µs, (note 2 & 3)	1375	А
P _{MAX}	Maximum power dissipation, IGBT (note 2)	16.1	kW
T _{j op}	Operating temperature range	-40 to +125	°C
T _{stg}	Storage temperature range	-40 to +125	°C

Notes: -

- 1) Unless otherwise indicated $T_j = 125^{\circ}C$.
- 2) $T_{sink} = 25^{\circ}C$, double side cooled.
- 3) Maximum commutation loop inductance 200nH.



Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V _{CE(sat)}	Collector – emitter saturation voltage	-	3.75	4.05	$I_C = 1375A, V_{GE} = 15V, T_j = 25^{\circ}C$	V
		-	5.10	5.40	$I_{C} = 1375A, V_{GE} = 15V$	V
V _{T0}	Threshold voltage	-	-	2.403	Current renge: 459A 1275A	V
r⊤	Slope resistance	-	-	2.18	Current range: 458A – 1375A	mΩ
$V_{\text{GE(TH)}}$	Gate threshold voltage	-	5.4	-	V _{CE} = V _{GE} , I _C = 1375mA	V
ICES	Collector – emitter cut-off current	-	9	30	$V_{CE} = V_{CES}, V_{GE} = 0V$	mA
Iges	Gate leakage current	-	-	±60	$V_{GE} = \pm 20V$	μA
Cies	Input capacitance	-	245	-	$V_{CE} = 25V, V_{GE} = 0V, f = 100kHz$	nF
t _{d(on)}	Turn-on delay time	-	1.3	-		μs
tr(V)	Rise time	-	3.2	-	I _C =1375A, V _{CE} =3600V, di/dt=3500A/μs	μs
Qg(on)	Turn-on gate charge	-	16	-	$V_{GE} = \pm 15V, L_s = 200nH$	μC
Eon	Turn-on energy	-	11.6	-	$R_{G(ON)}=2\Omega$, $R_{G(OFF)}=7.3\Omega$, $C_{GE}=100nF$	J
t _{d(off)}	Turn-off delay time	-	4.3	-	Freewheel diode type E1780TG65E at T _i =125°C	μs
t _f (I)	Fall time	-	2.1	-	(Notes 3, 4 & 5)	μs
Qg(off)	Turn-off gate charge	-	15.5	-		μC
Eoff	Turn-off energy	-	8.1	-		J
lsc	Short circuit current	-	6200	-	$\label{eq:VGE} \begin{array}{l} V_{\text{GE}} \mbox{=+}15\text{V}, \ V_{\text{CC}} \mbox{=-}3600\text{V}, \ V_{\text{CEmax}} \mbox{\leq-} V_{\text{CES}}, \\ t_p \mbox{\leq-} 10 \mbox{µs}, \ L_s \mbox{\leq-} 200n \mbox{H} \end{array}$	А

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
		-	-	6.21	Double side cooled	K/kW
R _{thJK}	Thermal resistance junction to sink, IGBT	-	-	9.68	Collector side cooled	K/kW
		-	-	18	Emitter side cooled	K/kW
F	Mounting force	45	-	55	Note 2	kN
Wt	Weight	-	2.2	-		kg

Notes:-

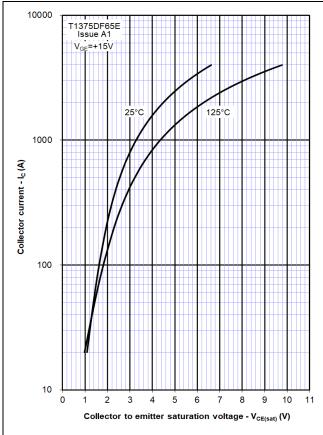
1) 2) 3) 4) 5)

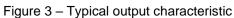
Unless otherwise indicated T_j=125°C. Consult application note 2008AN01 for detailed mounting requirements. C_{GE} is additional gate - emitter capacitance added to output of gate drive circuit. E_{on} integration time 15µs from 10% rising I_{G.} E_{off} integration time 15µs from 90% falling V_{GE.}

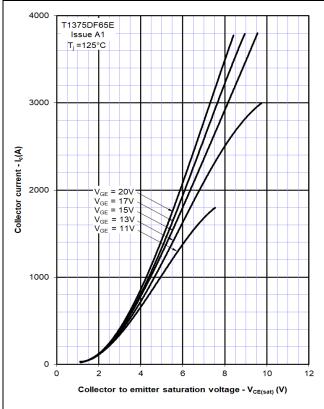


<u>Curves</u>

Figure 1 – Typical collector-emitter saturation voltage characteristics







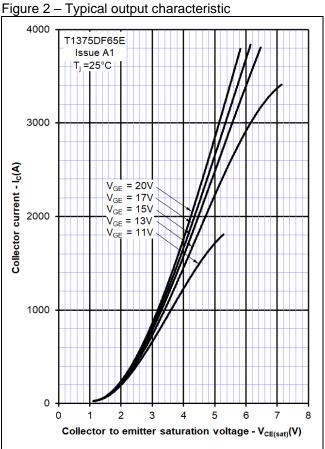


Figure 4 – Typical turn-on delay time vs gate resistance

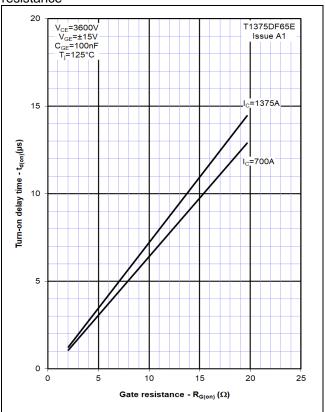
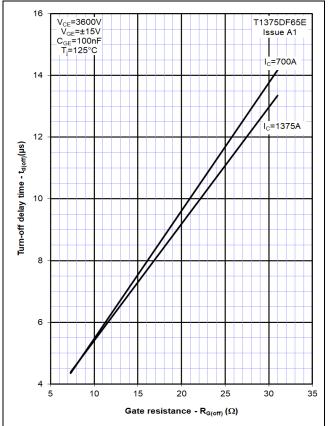
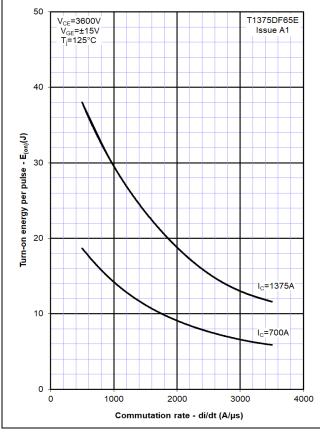




Figure 5 – Typical turn-off delay time vs. gate resistance







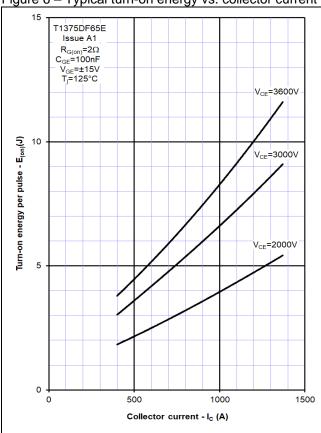


Figure 8 – Typical turn-off energy vs. collector current

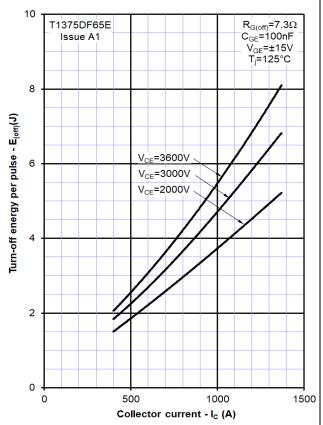


Figure 6 - Typical turn-on energy vs. collector current



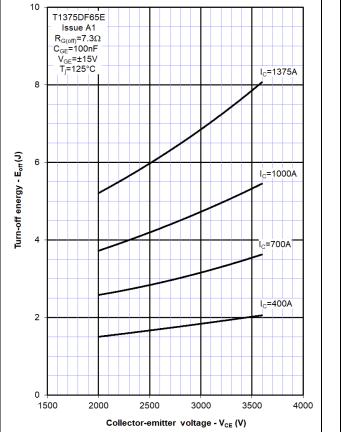


Figure 9 – Turn-off energy vs voltage

Figure 10 – Safe operating area

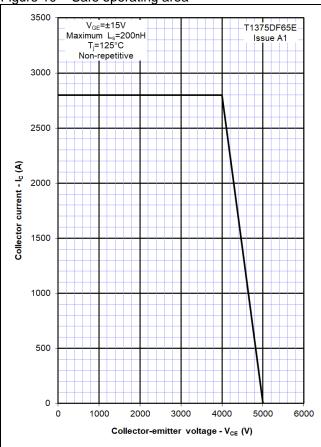
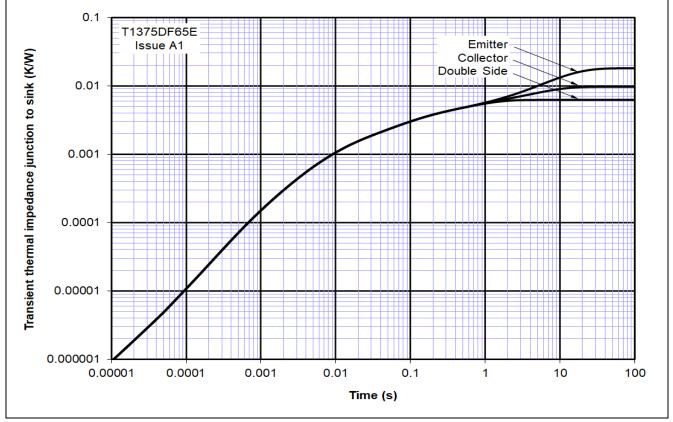
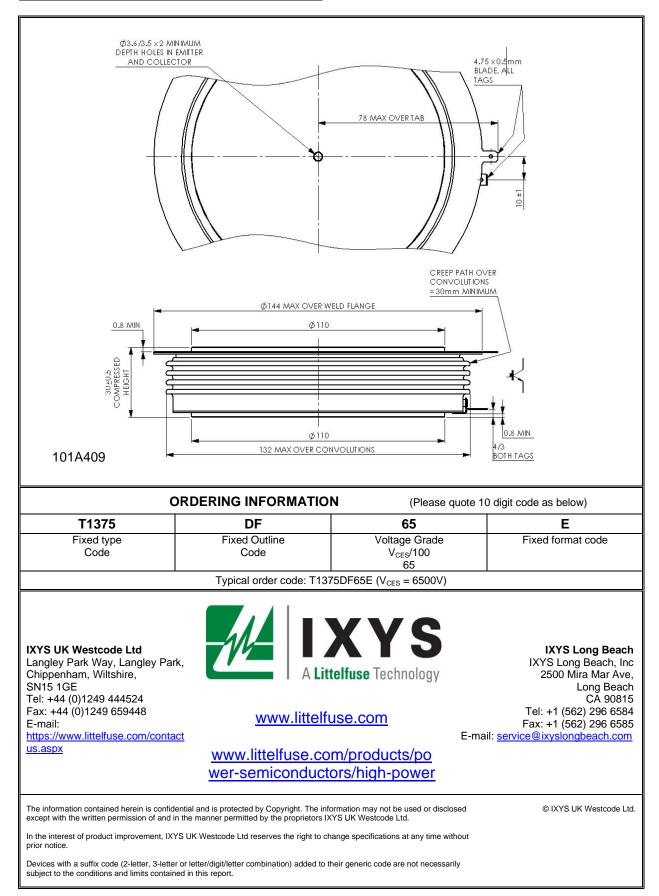


Figure 11 – Transient thermal impedance





Outline Drawing & Ordering Information





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